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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR		ATTORNEY DOCKET NO.	
09/435.76	6 11/08/99	KUSHIDA	Τ	104361	
OLIFF & BERRIDGE PLC		MMC1/0808		EXAMINER	
		File for a A common of	LOK	LOKE, S	
	9928 A VA 22320		ART UNIT	FAPER NUMBER	
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			DATE MAILE	<b>D:</b> 08/08/01	

Please find below and/or attached an Office communication concerning this application or proceeding.

**Commissioner of Patents and Trademarks** 

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## Office Action Summary

Application No. **09/435,766** 

Applicant(s)

Kushida

	Office Action Summary	Examiner-	Art Unit				
		Loke	2811				
	The MAILING DATE of this communication appears	on the cover sheet with the corres	spondence addre	988			
	for Reply						
THE N	ORTENED STATUTORY PERIOD FOR REPLY IS SET MAILING DATE OF THIS COMMUNICATION.						
aft - If the be	sions of time may be available under the provisions of 37 C ter SIX (6) MONTHS from the mailing date of this communic period for reply specified above is less than thirty (30) days considered timely. period for reply is specified above, the maximum statutory	cation. s, a reply within the statutory minimun	n of thirty (30) da	ays will			
- Failur - Any r ea	mmunication. The to reply within the set or extended period for reply will, by the office later than three months after the rned patent term adjustment. See 37 CFR 1.704(b).						
Status 1) 💢	Responsive to communication(s) filed on Jun 4, 20	001		·			
2a) 🗌	This action is <b>FINAL</b> . 2b) 💢 This ac	tion is non-final.					
3) 🗆	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11; 453 O.G. 213.						
Disposi	tion of Claims						
4) 💢	Claim(s) 1-4 and 12	is/are	e pending in the	e application.			
4	la) Of the above, claim(s)	is/ar	e withdrawn fi	rom consideration.			
5) 💢	Claim(s) <u>12</u>		is/are allowed.				
6) 💢	Claim(s) <u>1-4</u>		is/are rejected	,			
7) 🗆	Claim(s)		is/are objected	i to.			
8) 🗆	Claims	are subject to restric	ction and/or ele	ection requirement.			
Applica	tion Papers						
9) 🗆	The specification is objected to by the Examiner.			•			
10)	The drawing(s) filed on is/are	e objected to by the Examiner.					
11)	)☐ The proposed drawing correction filed on is: a)☐ approved b)☐ disapproved.						
12)	The oath or declaration is objected to by the Exam	niner.		•			
13) 🗆	under 35 U.S.C. § 119  Acknowledgement is made of a claim for foreign $p$ All $b$ ) $\square$ Some* $c$ ) $\square$ None of:	oriority under 35 U.S.C. § 119(a)	-(d).				
	1. $\square$ Certified copies of the priority documents have	ve been received.					
	2. Certified copies of the priority documents have			·			
	3. ☐ Copies of the certified copies of the priority of application from the International Bure ee the attached detailed Office action for a list of the action for a li	eau (PCT Rule 17.2(a)).	this National S	Stage			
14)			e).				
Attachm	ent(s)			. <b>.</b>			
15) 🔲 N	otice of References Cited (PTO-892)	18) Interview Summary (PTO-413) Paper	No(s)	•			
16) 🔲 N	otice of Draftsperson's Patent Drawing Review (PTO-948)	19) Notice of Informal Patent Application (PTO-152)					
17) 🔲 In	formation Disclosure Statement(s) (PTO-1449) Paper No(s).	20) Other:					

Application/Control Number: 09/435766

Art Unit: 2811

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1 and 3 are rejected under 35 U.S.C. 102(b) as being clearly anticipated by Terashima.

In regards to claim 1, Terashima shows all the elements of the claimed invention in figs. 1 and 14. It is a semiconductor device, comprises: an electrode [10]; a region [2] having a first conductive type (p-type) and disposed on the electrode [10]; a region [1] having a second conductive type (n-type) and disposed on the p-type region [2]; a channel region [1] (protruding portion [3]) having the second conductive type (n-type) and disposed on the region [1]; a gate region [6] provided so as to surround at least a part of the channel region [1] via an insulation film [5]; a region [4] having the second conductive type (n-type) provided on the channel region [1], the region [4] is located substantially at a center of the channel region [1], and the region [4] is isolated from the insulation film [5]; and an electrode [9] connected to the region [4].

In regards to claim 3, Terashima shows a semiconductor region [13] having the first conductive type (p-type) provided between the channel region [1] and the electrode [9].

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are

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Art Unit: 2811

such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

4. Claims 2 and 4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Terashima.

In regards to claim 2, it would have been obvious for the gate region has the first conductive type (p-type) because it is a conventional gate electrode material.

In regards to claim 2, Terashima shows a depletion layer is formed over most of the entire channel region when a predetermined voltage is applied to the gate region (col. 8, lines 5-16).

In regards to claim 4, Terashima shows a semiconductor region [13] having the first conductive type (p-type) provided between the channel region [1] and the electrode [9].

- 5. Claim 12 is allowed.
- 6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Steven Loke whose telephone number is (703) 308-4920.

sl

August 7, 2001

Steven Loke Primary Examiner

THE PERSON NAMED IN COLUMN TWO IS NOT THE OWNER.

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